

AMENDMENTS TO THE SPECIFICATION

On page 1, line 4, please insert the following paragraph:

- - This application claims the benefit of co-pending P.C.T. Application No.

PCT/US2003/05314, filed on February 20, 2003, and hereby incorporated herein by reference. - -

On page 9, paragraph 30, line 4, please make the following change:

[0030] If there is a high-resistance short type defect between a dynamic floating node and a signal line connected to the drain of an active n-transistor 16 (FIG. 1), the discharge of the node will be strongly affected by the RC constant determined by the equivalent resistance of n-transistor 16 and the capacitance on the dynamic node. ~~Increasing~~ Decreasing V_t will decrease the equivalent resistance of n-transistor 16 and therefore make the discharge faster and, therefore, easier to detect. Note that increasing V_{dd} would similarly decrease the equivalent resistance of n-transistor 16, but would present a higher charge Q to be discharged in the first place (charge Q = capacitance C times V_{dd}), which makes detection harder.

By this Preliminary Amendment a new paragraph has been added to page 1 of the subject application to claim priority to a PCT application and paragraph 30 has been revised. No new matter is believed added.

Applicant respectfully submits that the Application as presented is in condition for examination. Should the Examiner believe that anything further is necessary in order to place the application in better condition for examination, the Examiner is requested to contact Applicant's undersigned attorney at the telephone number listed below.

Respectfully submitted,



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